

# Results with the ALICE CMOS investigator chip

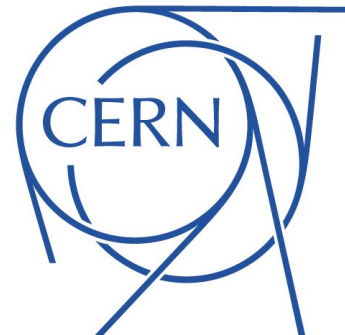
Magdalena Munker (CERN, University of Bonn)

Dominik Dannheim (CERN)

Andreas Nurnberg (CERN)

CLICdp collaboration meeting

March 9<sup>th</sup> 2017



# Outline



- Motivation of monolithic technology for the CLIC tracker
- The ALICE Investigator Chip
- Test-beam:
  - Setup
  - Analysis
  - Results
- Simulation
- Summary & outlook

## Large surface silicon tracker planned for CLIC ( $\sim 100\text{m}^2$ ):

- Need of large scale production

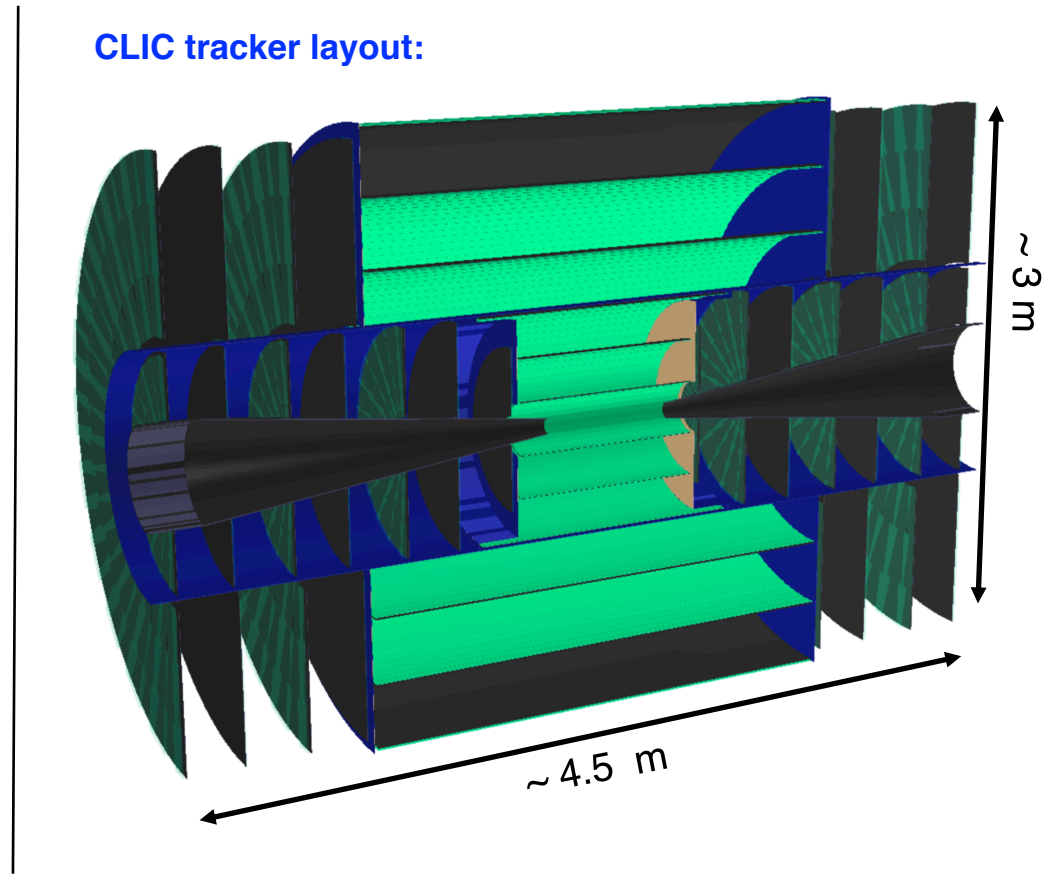
## Benefit from **monolithic technologies**:

- Electronics integrated in sensor
- No separate readout chip
- No need of bump bonding
- Reduced material budget

## Benefit from **synergies with ALICE** collaboration:

- Test-chip developed within ALICE collaboration to investigate full analogue performance of monolithic technology chosen by ALICE
- Interesting to study feasibility of technology chosen by ALICE with respect to CLIC tracker requirements  
(time slicing of 10 ns, single point resolution of  $\sim 7 \mu\text{m}$ )

## CLIC tracker layout:



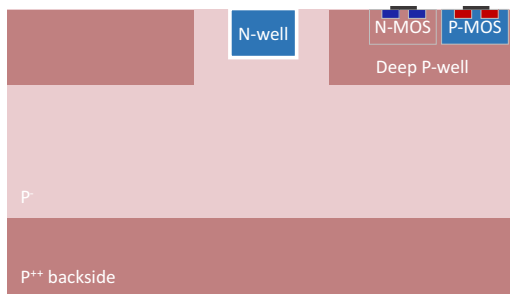
# The ALICE Investigator chip (*W. Snoeys, J.W. van Hoorne et. al.*)



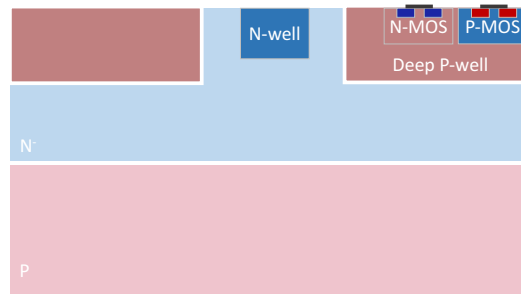
## Monolithic HR-CMOS process:

- Developed as part of ALPIDE development for ALICE ITS upgrade
- 180 nm High Resistivity (HR) CMOS process, 15-40  $\mu\text{m}$  thick epitaxial layer (1-8  $\text{k}\Omega\text{cm}$ )
- Two different submissions, changes in 2<sup>nd</sup> submission to achieve full depletion of epitaxial layer:

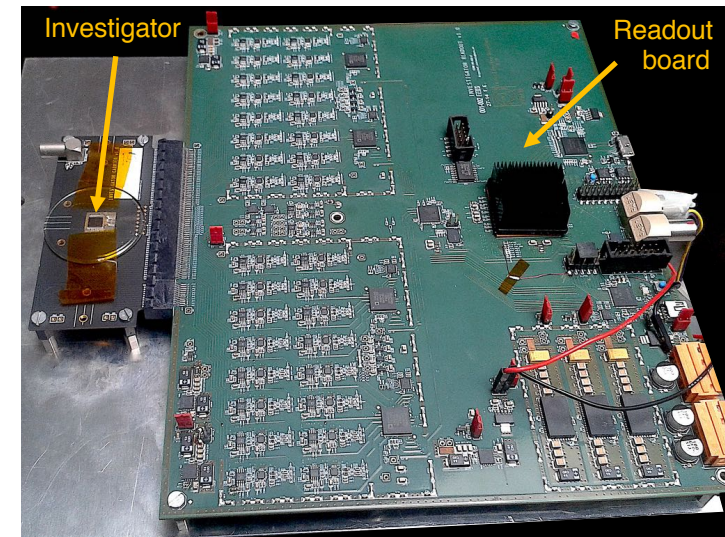
Schematic of process cross section of **standard process**:



Schematic of process cross section of **modified process**:



Investigator & external readout board:

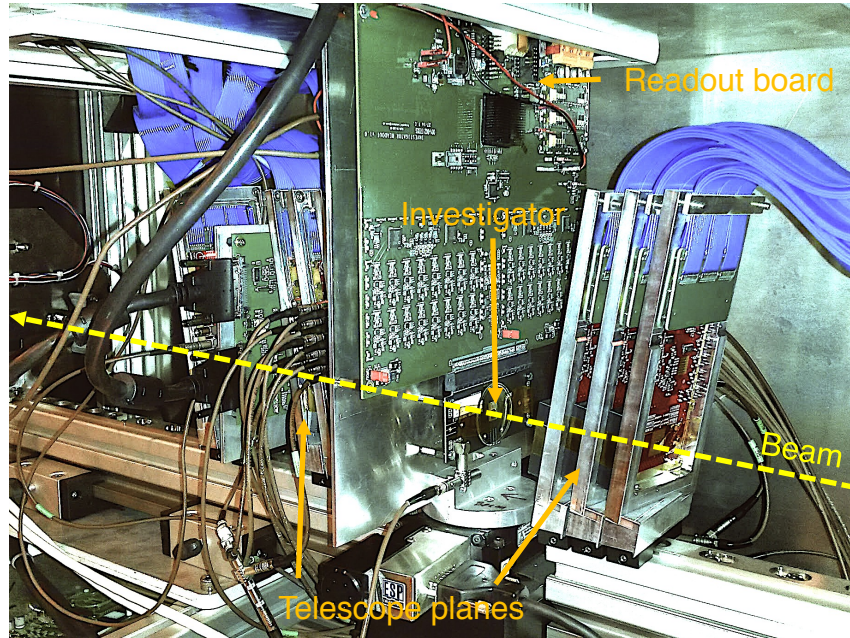


## Test chip:

- Different mini-matrixes with 8x8 pixels
- Various pixel layouts to optimise the collection-diode geometry:
  - Minimise capacitance ( $\sim 2$  fF)  $\leftrightarrow$  fast timing ( $\sim$  ns)
- External readout board (*designed by K. M. Sielewicz*)
- 64 ADCs to read out full waveform of 8x8 pixel matrix
- 65 MHz sampling clock limits achievable timing resolution

## ALICE INVESTIGATOR integrated in CLICdp Timepix3 telescope at SPS beam-line:

### Test-beam setup:



Benefit from good timing & spatial resolution of Timepix3 telescope:

- Timing resolution  $\sim$  ns
- Single point tracking resolution on DUT  $\sim$  2  $\mu$ m

### Synchronisation of Investigator & telescope data:



If at least one pixel crosses a threshold of signal/noise  $>$  8:

- Store waveform from all pixels
- Sent time stamp to telescope planes
- Used for offline synchronisation

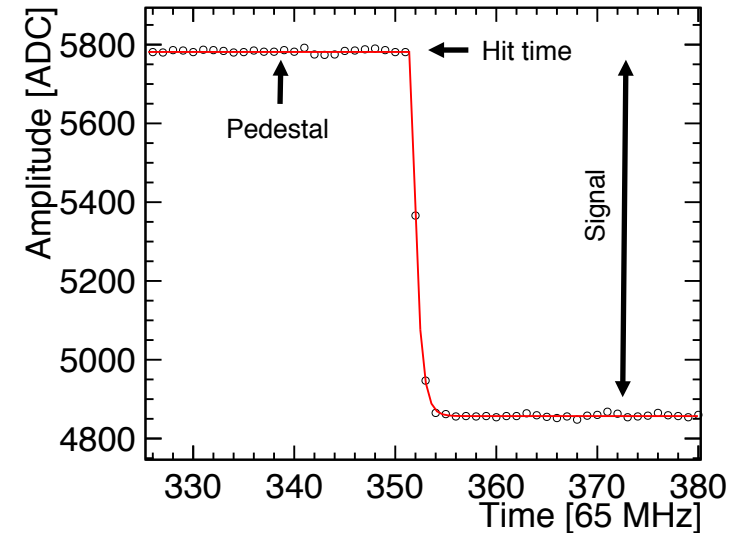
Note: veto of telescope planes during dead times of Investigator to avoid bias in efficiency

## Investigator event reconstruction:

- Signal defined as magnitude of amplitude drop
- Noise defined as RMS of fluctuation around baseline
- Cut on  $S/N > 5$  for each single pixel
- Fit exponential function  $f(t)$  to waveform of each pixel to extract exact timing and signal:

$$f(t) = \begin{cases} \text{Pedestal} & t \leq t(\text{hit}) \\ \text{Pedestal} + \text{Signal} * (e^{-[t-t(\text{hit})] / t(\text{rise})} - 1) & t > t(\text{hit}) \end{cases}$$

Example of pixel waveform fit:



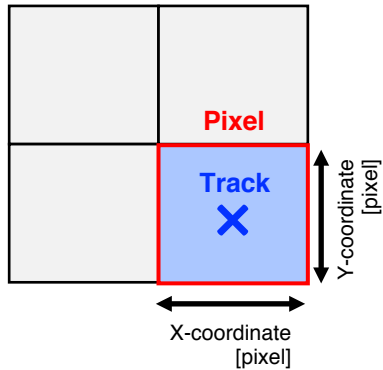
## Quality cuts:

- Distance between track and Investigator hit  $< 2$  pixel
- Masking of half of edge pixels

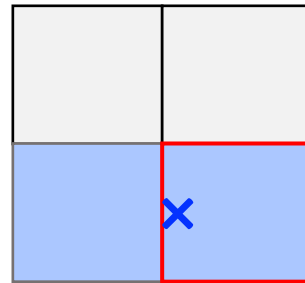
Investigation of track position in pixel for different cluster sizes to study charge sharing on sub pixel level:

## Geometrical expectation:

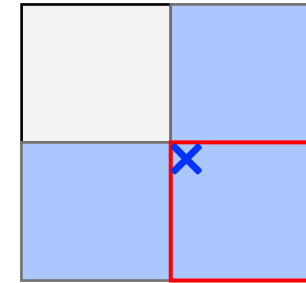
Cluster size 1:



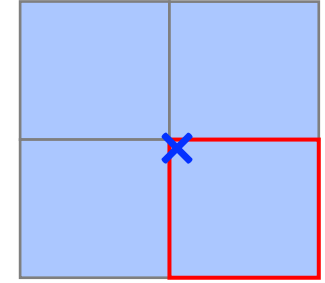
Cluster size 2:



Cluster size 3:



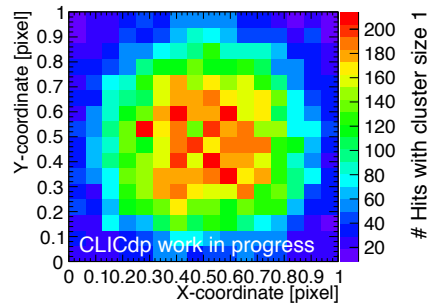
Cluster size 4:



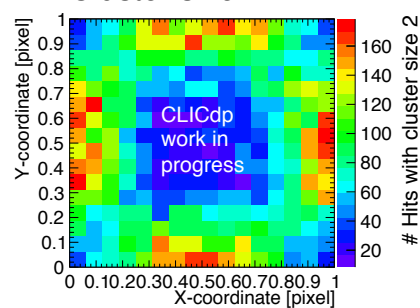
## Results for pixel size 28 $\mu\text{m}$ , bias voltage 6 V, 25 $\mu\text{m}$ epi-thickness, modified process:

Seed threshold  $\sim 140 e^-$ , neighbor threshold  $\sim 50 e^-$

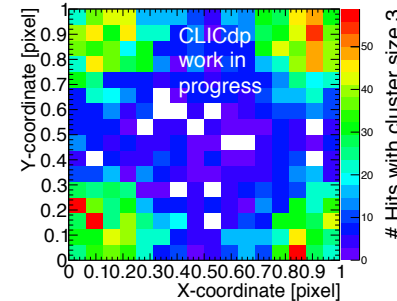
Cluster size 1:



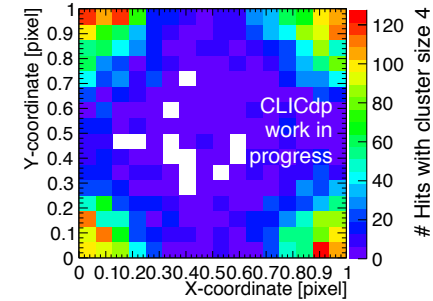
Cluster size 2:



Cluster size 3:



Cluster size 4:

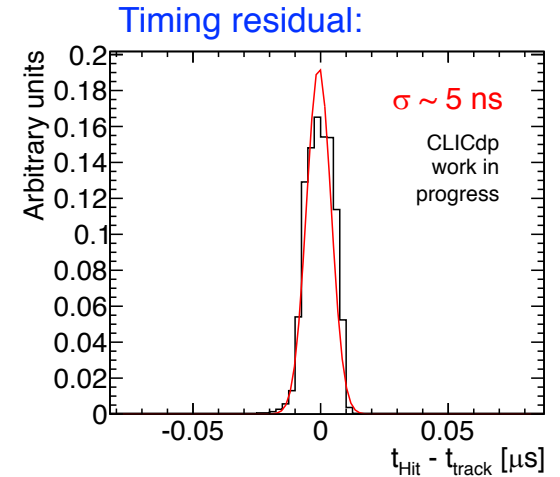
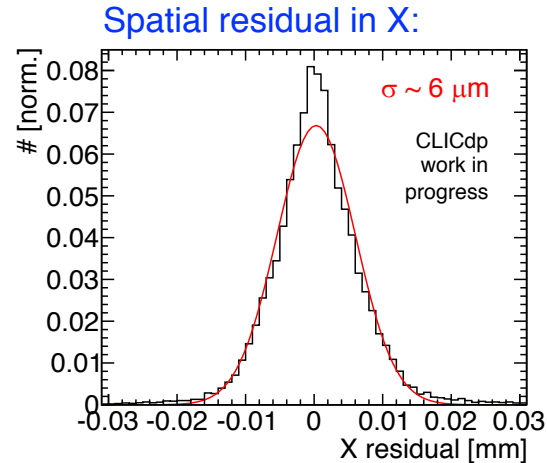
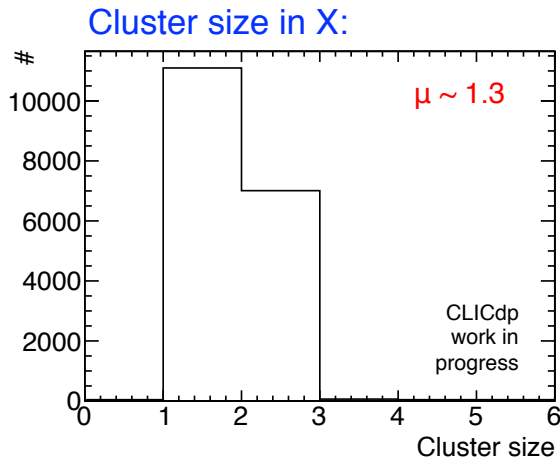


→ Benefit from good tracking resolution of CLICdp Timepix3 telescope

→ *Detailed understanding of charge sharing on sub pixel level*

**Results for pixel size 28  $\mu\text{m}$ , bias voltage 6 V, 25  $\mu\text{m}$  epi-thickness modified process:**

Seed threshold  $\sim 140 e^-$ , neighbor threshold  $\sim 50 e^-$



- Spatial reconstruction by charge interpolation and  $\eta$ -correction to correct for non-linear charge sharing
- Charge sharing leads to improved spatial resolution of  $\sim 6 \mu\text{m}$  (binary expectation  $\sim 8 \mu\text{m}$ )
- Timing residual determined by difference between hit time of first pixel in cluster and mean track time
- Timing resolution of  $\sim 5 \text{ ns}$  (note: limited by sampling frequency of 65 MHz)
- *Spacial & timing resolution well within requirements for CLIC tracker (external readout)*

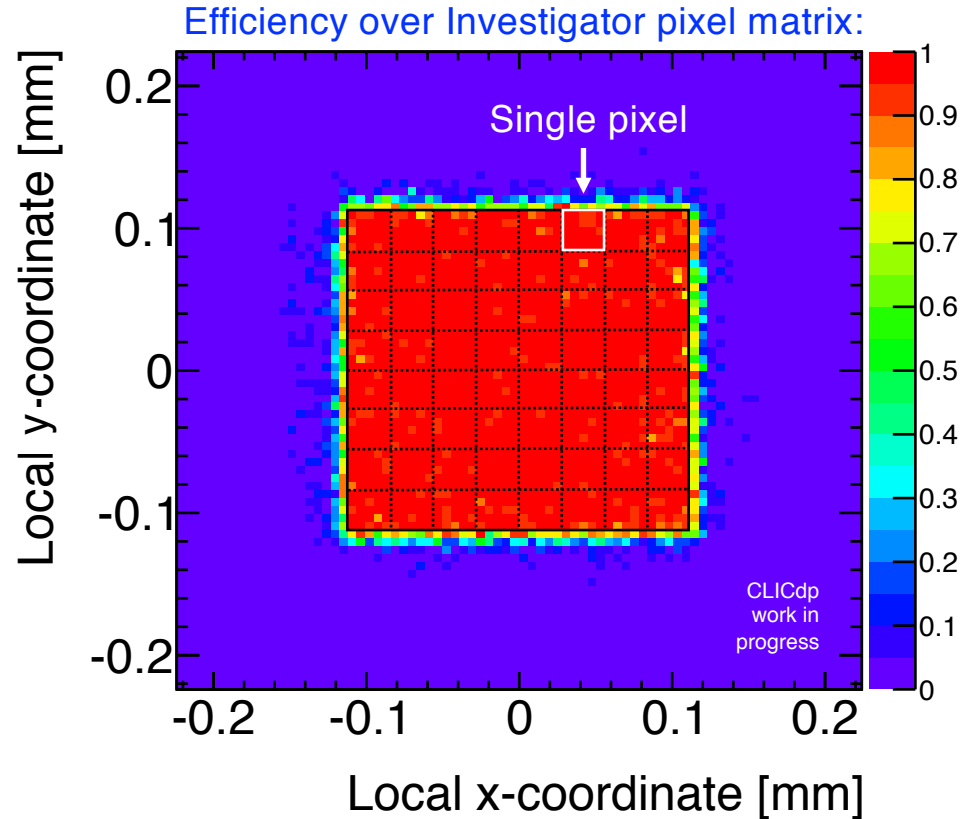


## Results for pixel size 28 $\mu\text{m}$ , bias voltage 6 V, 25 $\mu\text{m}$ epi-thickness modified process:

Seed threshold  $\sim 140 e^-$ , neighbor threshold  $\sim 50 e^-$

### If a track is reconstructed through the Investigator:

- If Investigator hit within distance of 2 pixels from track  
→ Count 1 for efficiency
- If NO Investigator hit within distance of 2 pixels from track  
→ Count 0 for efficiency
- Histogram filled at local track position extrapolated on Investigator



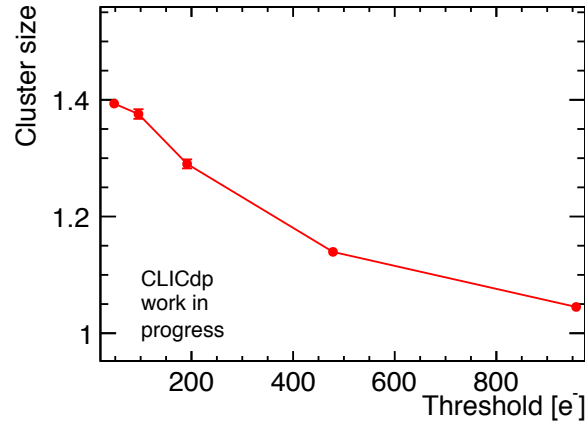
- Global efficiency of  $\sim 99.3\%$  (after masking of half of edge pixels, study ongoing)

→ *Good performance in full phase space*

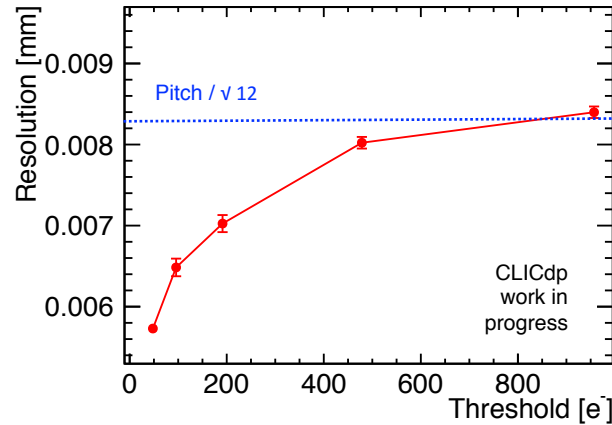
## Results for pixel size 28 $\mu\text{m}$ , bias voltage 6 V, 25 $\mu\text{m}$ epi-thickness modified process:

Calibration with Fe-source applied to convert threshold to  $e^-$

Cluster size vs. threshold:



Resolution vs. threshold:

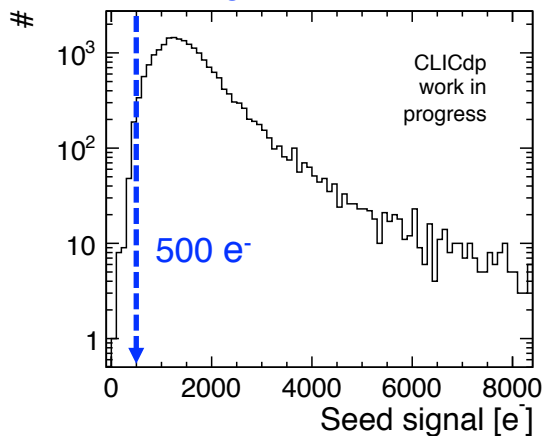


General dependency:

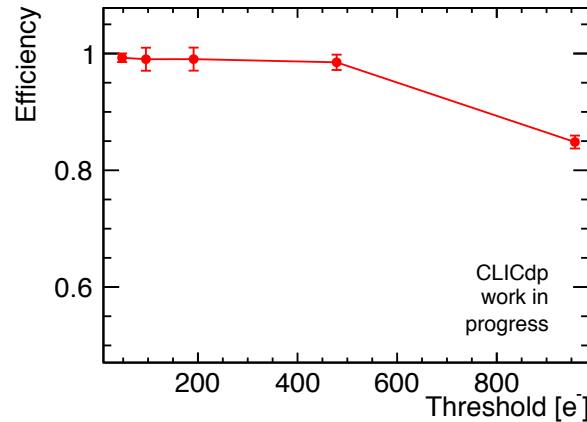
Cut into neighbor signal:

- Decrease of cluster size
- Degradation of resolution until binary limit

Seed signal :



Efficiency vs. threshold:



Very high threshold > 500  $e^-$ :

Cut into seed signal:

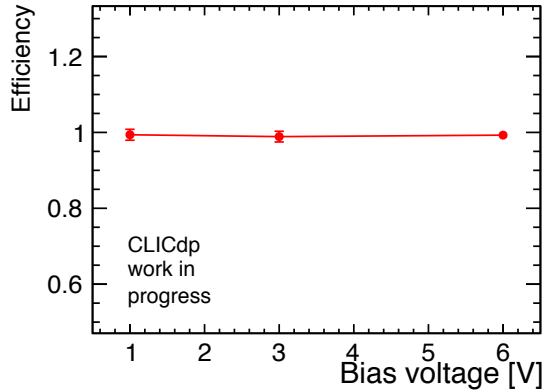
- Decrease of efficiency

→ Need low threshold to gain in resolution and be fully efficient

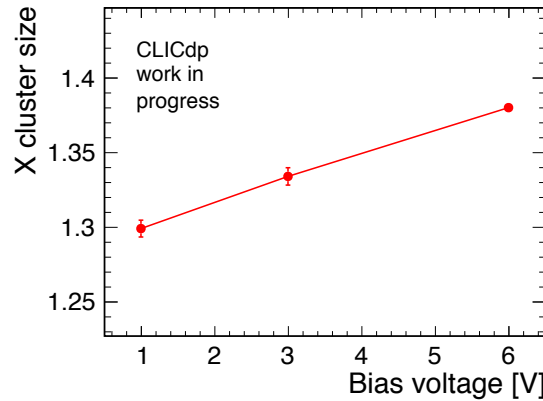
## Results for pixel size 28 $\mu\text{m}$ , 25 $\mu\text{m}$ epi-thickness modified process:

Calibration with Fe-source applied to convert threshold to  $e^-$

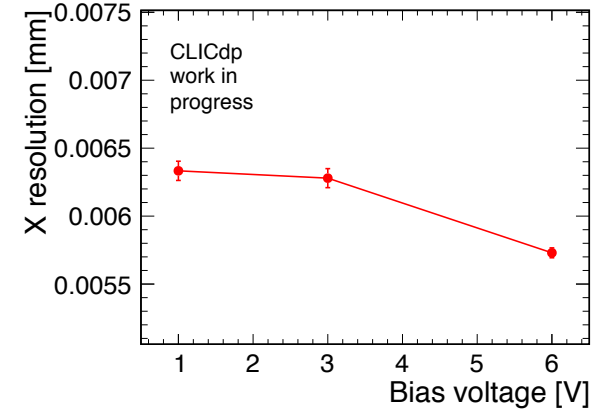
### Efficiency vs. bias:



### Cluster size X vs. bias:

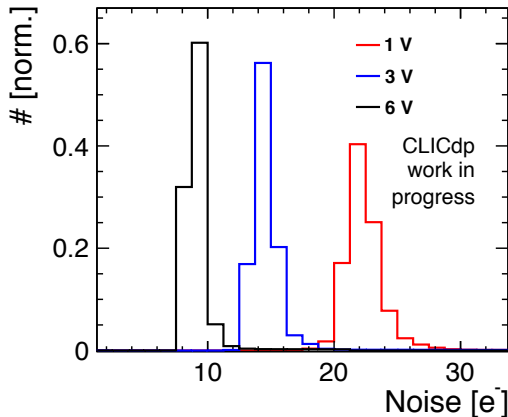


### X resolution vs. bias:

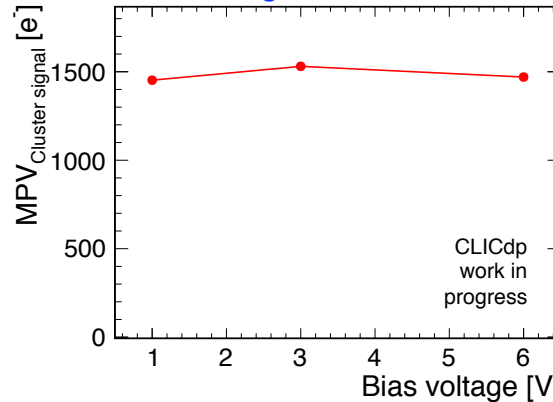


- No significant changes in efficiency
- Lower cluster size and worse resolution for low bias:

### Noise for different bias:



### Cluster signal vs. bias:



- Higher noise for lower bias voltage due to higher input capacitance for lower voltage
- No significant changes in signal
- Higher cut on signal/noise
- Less charge sharing for lower bias because of higher threshold

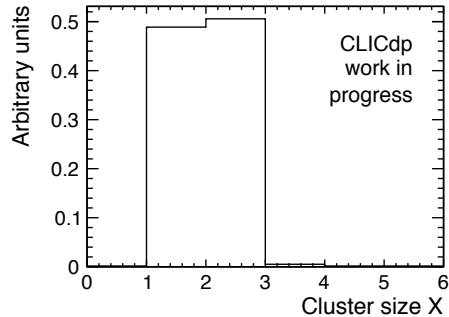
→ Need high bias to achieve low noise to be able to push the threshold to low values and gain in resolution

# Comparison of two different submissions

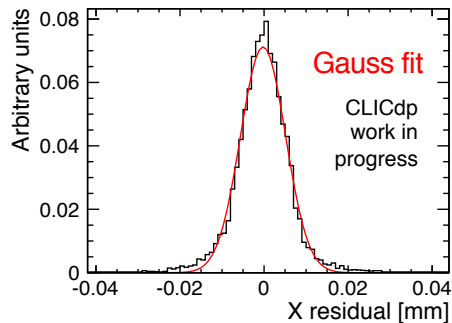


Results for pixel size 28  $\mu\text{m}$ , bias voltage 6 V  
standard process:

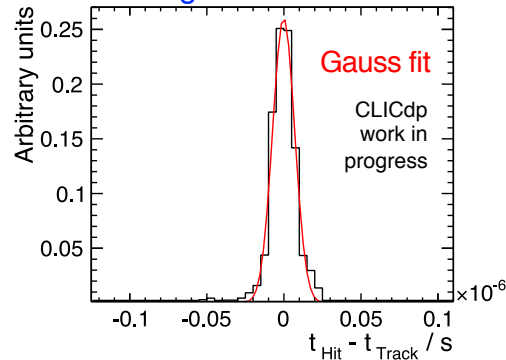
Cluster size X:



Spatial residual X:



Timing residual :

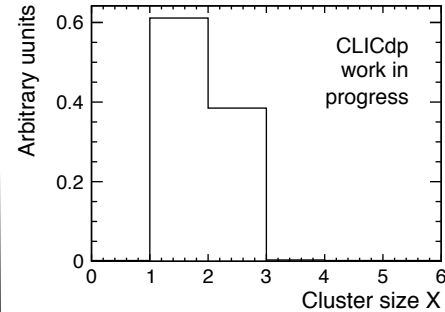


Summary table:

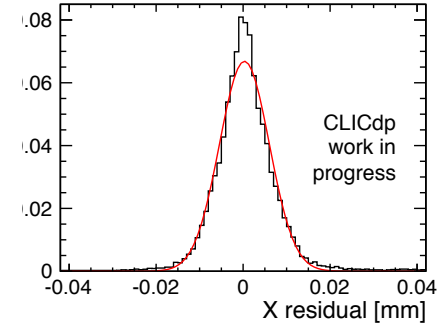
Cluster size X	1.5
Spatial resolution X [ $\mu\text{m}$ ]	5
Timing resolution ns	7
Seed threshold [ $e^-$ ]	200
Neighbor threshold [ $e^-$ ]	70
Epi thickness [ $\mu\text{m}$ ]	18

Results for pixel size 28  $\mu\text{m}$ , bias voltage 6 V  
modified process:

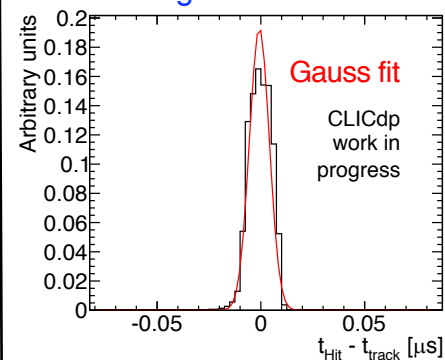
Cluster size X:



Spatial residual X:



Timing residual :



Summary table:

Cluster size X	1.3
Spatial resolution X [ $\mu\text{m}$ ]	6
Timing resolution ns	5
Seed threshold [ $e^-$ ]	140
Neighbor threshold [ $e^-$ ]	50
Epi thickness [ $\mu\text{m}$ ]	25

Magenta = main different parameters

Changes in second submission to achieve full depletion:

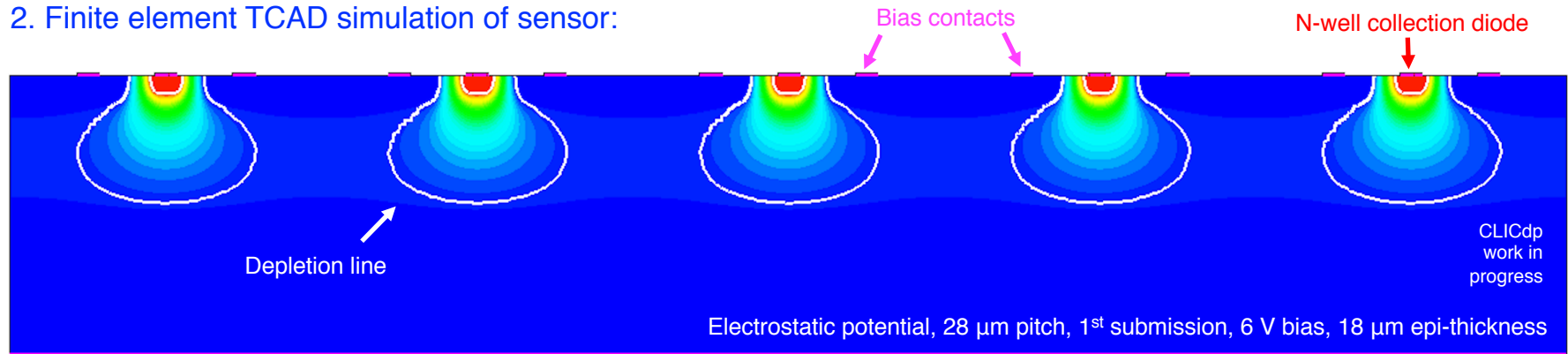
- Expect that less diffusion results in lower cluster size & faster timing
- *Despite thicker epi layer for modified process, lower cluster size and faster timing compared to standard process*

## Simulation chain:

1. Geant4 simulation of energy deposit in silicon



2. Finite element TCAD simulation of sensor:



- Simulate sensor geometry, doping and bias application
- Transient simulation using particle with energy deposit from GEANT4
- Scan particle incident position over unit cell, representing full physical problem and calculate induced charge

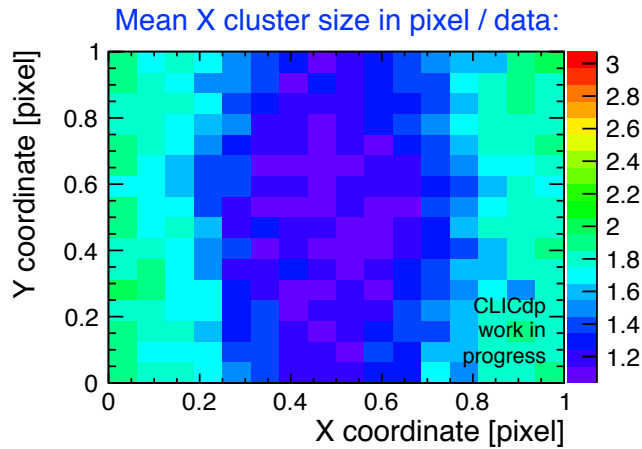


3. Fast model of threshold application, energy fluctuations, telescope resolution and reconstruction

# Comparison of simulation & data



## Comparison of 3d-data and 2d-simulation:

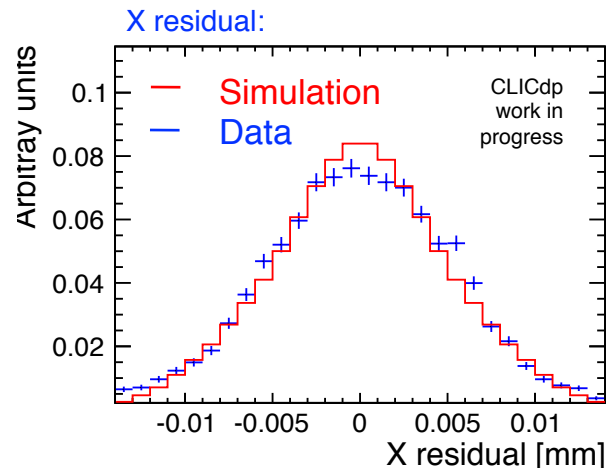
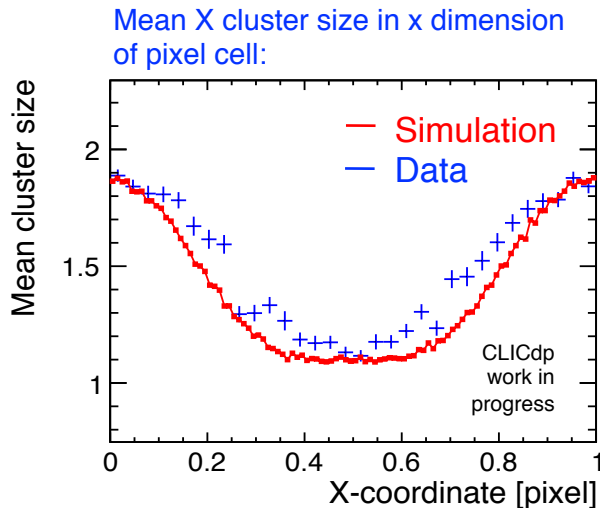


Observation:

- Charge sharing in X does not change significantly along Y dimension of pixel
- ➔ Can compare X-cluster size in pixel and X-residual between data and simulation (*approximation*)

## Comparison of simulation & data, pixel size 28 $\mu\text{m}$ , bias voltage 6 V, 18 $\mu\text{m}$ epi-thickness standard process:

Seed threshold  $\sim 200 e^-$ , neighbor threshold  $\sim 70 e^-$



- Calibration applied to define threshold in simulation
- ➔ *Good agreement of simulation in X residual and in-pixel X cluster size*

# Summary & outlook



## Investigator HR-CMOS process studied in various test-beam campaigns:

- Charge sharing on in-pixel level well understood
  - Bias and threshold scan performed
  - Qualitative comparison of different submissions
  - Overall performance meeting requirements for CLIC Tracker:
    - Single point resolution  $\sim 6 \mu\text{m}$
    - Efficiency  $\sim 99.3 \%$   
(study ongoing)
    - Timing resolution  $\sim 5 \text{ ns}$
- Results for modified process  
28  $\mu\text{m}$  pixel size  
Test-chip with external readout
- Studies used as input for design of fully monolithic tracker chip for CLIC  
(see Iraklis talk in this session: *An overview of CMOS sensor technologies for CLIC*)

## Simulation of standard process:

- Validated with test-beam data ongoing, good agreement so far
- Can be used to investigate performance for different pixel layouts